May 2015



FCPF220N80

N-Channel SuperFET $^{\circledR}$ II MOSFET 800 V, 23 A, 220 m $_{\Omega}$

Features

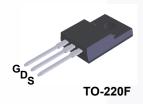
- Typ. $R_{DS(on)}$ = 188 m Ω
- Ultra Low Gate Charge (Typ. Q_q = 78 nC)
- Low E_{oss} (Typ. 7.5 uJ @ 400 V)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 304 pF)
- · 100% Avalanche Tested
- RoHS Compliant
- · ESD Improved Capability

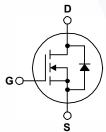
Applications

- · AC-DC Power Supply
- · LED Lighting

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FCPF220N80	Unit
V _{DSS}	Drain to Source Voltage			800	V
\/	Cata to Sauraa Valtaga	- DC		±20	V
V _{GSS} Gate to Source Volta	Gate to Source Voltage	- AC	(f >1 Hz)	±30	V
	Drain Current	- Continuous (T _C = 25°C)		23*	
Drain Current	- Continuous (T _C = 100°C)		14.6*	Α	
I _{DM}	Drain Current	- Pulsed	(Note 1)	57*	Α
E _{AS}	Single Pulsed Avalanche En	ergy	(Note 2)	645	mJ
I _{AR}	Avalanche Current		(Note 1)	4.6	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		27.8	mJ	
dv/dt	MOSFET dv/dt			100	V/ns
uv/ut	Peak Diode Recovery dv/dt		(Note 3)	20	V/IIS
D	Bower Dissination	(T _C = 25°C)		44	W
P _D Power Dissipation	- Derate Above 25°C		0.35	W/°C	
T _J , T _{STG}	Operating and Storage Temp	perature Range		-55 to +150	°C
T _L	Maximum Lead Temperature 1/8" from Case for 5 Second	.		300	°C

^{*}Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter FCPF220N80			
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.8	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	*C/VV	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF220N80	FCPF220N80	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^{\circ}\text{C}$	800	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.8	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 800 V, V _{GS} = 0 V	-	-	25	
I _{DSS}	Zelo Gate Voltage Diam Current	$V_{DS} = 640 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	250	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.3 \text{ mA}$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 11.5 A	-	188	220	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 11.5 A	-	25	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V = 400 V V = 0 V	\-	3430	4560	pF
C _{oss}	Output Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz		100	135	pF
C _{rss}	Reverse Transfer Capacitance			0.3	-	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1 MHz		49	-	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V		304	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	$V_{DS} = 640 \text{ V}, I_{D} = 23 \text{ A},$	-	78	105	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	16	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	28	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	0.78	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time		- /	27	64	ns
t _r		$V_{DD} = 400 \text{ V}, I_D = 23 \text{ A},$	- /	19	48	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_g = 4.7 \Omega$	-	75	160	ns
t _f	Turn-Off Fall Time	(Note 4)	_	2.6	15	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current			-	23	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	57	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 23 A		-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 23 A,	-	560	-	ns
Q _{rr}	Reverse Recovery Charge dI _F /dt = 100 A/μs		-	14	-	μС

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_{AS} = 4.6 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C.
- 3. $I_{SD} \le 23$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T $_J$ = 25°C.
- Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

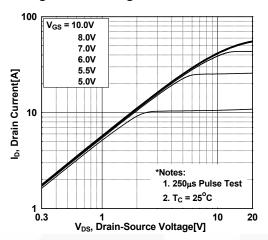


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

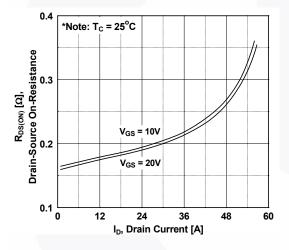


Figure 5. Capacitance Characteristics

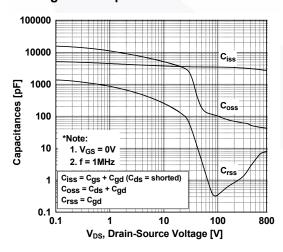


Figure 2. Transfer Characteristics

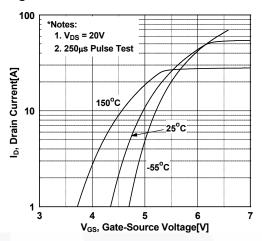


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

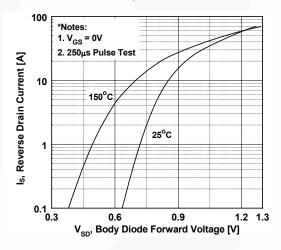
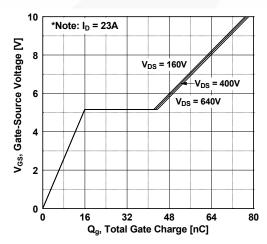


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

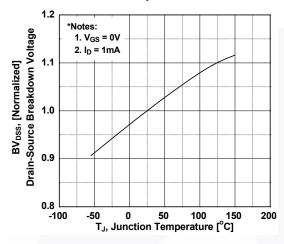


Figure 9. Maximum Safe Operating Area

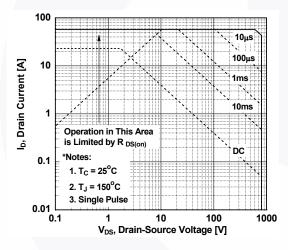


Figure 11. Eoss vs. Drain to Source Voltage

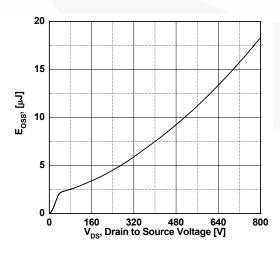


Figure 8. On-Resistance Variation vs. Temperature

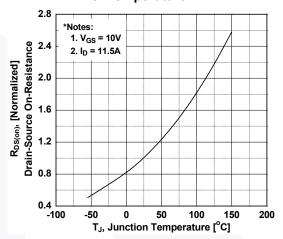
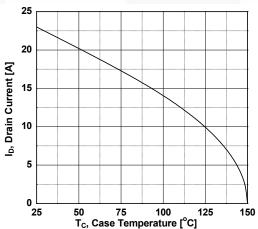
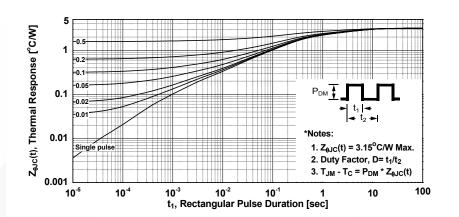


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



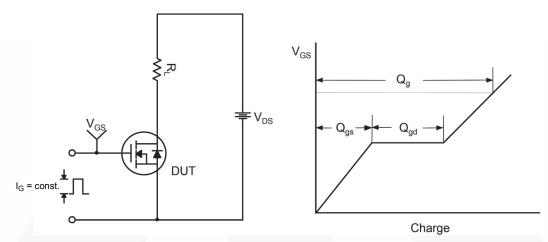


Figure 13. Gate Charge Test Circuit & Waveform



Figure 14. Resistive Switching Test Circuit & Waveforms

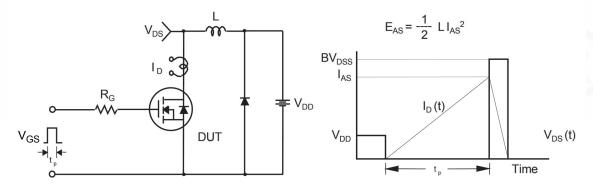


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

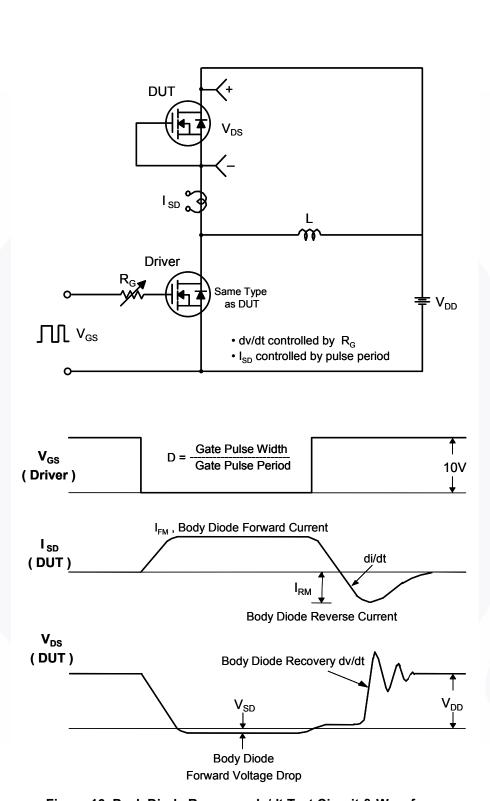
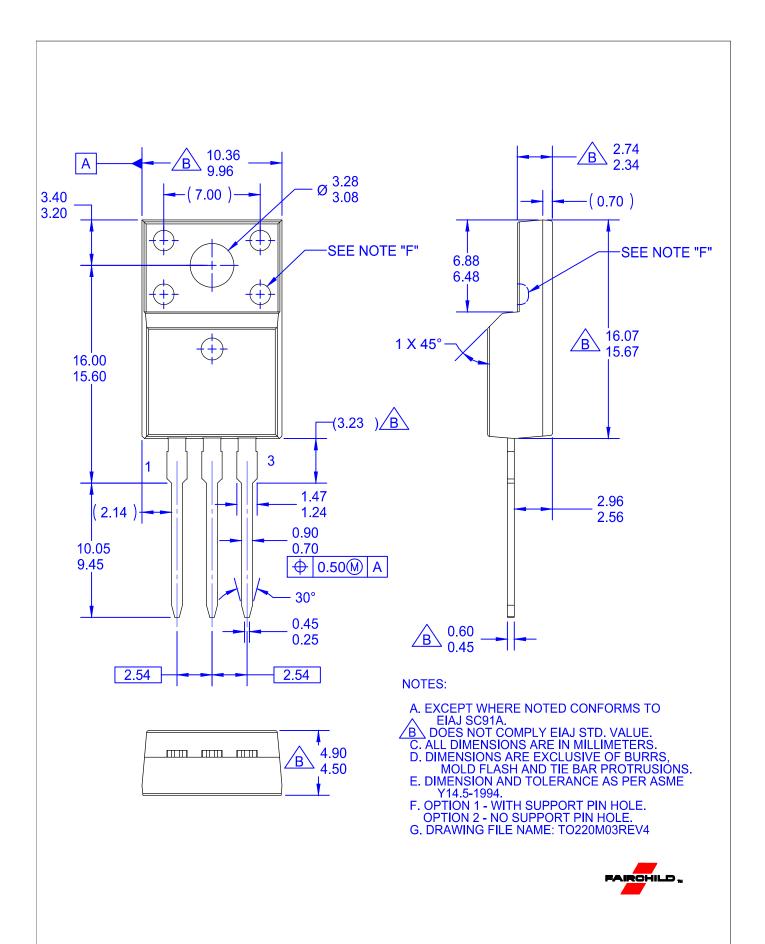


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms







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